



SST12LP17E is a 2.4 GHz high-efficiency, fully-matched power amplifier module based on the highly-reliable InGaP/GaAs HBT technology. It is designed in compliance with IEEE 802.11b/g/n applications and typically provides 28 dB gain with 28% power-added efficiency at 21dBm. SST12LP17E has excellent linearity, providing 3% EVM at typically 18 dBm, while meeting 802.11g spectrum mask at 21.5 dBm. This power amplifier requires no external RF matching, and only requires one external DC-bias capacitor to meet the specified performance. It offers high-speed power-up/-down control through a single reference voltage pin and includes a temperature-stable, VSWR insensitive power detector voltage output. SST12LP17E is offered in a super-thin (0.4mm maximum) 8-contact X2SON package and a 8-contact USON package.

Features

- **Input/Output ports internally matched to 50Ω and DC decoupled**
- **High gain:**
 - Typically 28 dB gain across 2.4–2.5 GHz
- **High linear output power:**
 - >24 dBm P1dB
 - Single-tone measurement. Please refer to “Absolute Maximum Stress Ratings” on page 5
 - Meets 802.11g OFDM ACPR requirement up to 21.5 dBm
 - ~3% added EVM up to 18 dBm for 54 Mbps 802.11g signal
 - Meets 802.11b ACPR requirement up to 22 dBm
- **High power-added efficiency/Low operating current for both 802.11b/g/n applications**
 - ~28%/138 mA @ P_{OUT} = 21.5 dBm for 802.11g
 - ~33%/155 mA @ P_{OUT} = 22.5 dBm for 802.11b
- **Single-pin low I_{REF} power-up/down control**
 - I_{REF} <2 mA
- **Low idle current**
 - ~60 mA I_{CQ}
- **High-speed power-up/down**
 - Turn on/off time (10%- 90%) <100 ns
 - Typical power-up/down delay with driver delay included <200 ns
- **Low shut-down current (~2 μA)**
- **Stable performance over temperature**
 - ~2 dB gain variation between -40°C to +85°C
 - ~1 dB power variation between -40°C to +85°C
- **Excellent on-chip power detection**
 - >15 dB dynamic range, dB-wise linear
 - VSWR insensitive, temperature stable
- **Packages available**
 - 8-contact X2SON – 2mm x 2mm x 0.4mm
 - 8-contact USON – 2mm x 2mm x 0.6mm
- **Non-Pb (lead-free), RoHS compliant, and Halogen free**

Applications

- WLAN (IEEE 802.11b/g/n)
- Home RF
- Cordless phones
- 2.4 GHz ISM wireless equipment



Product Description

The SST12LP17E is a versatile power amplifier based on the highly-reliable InGaP/GaAs HBT technology. The input/output RF ports are fully matched to 50Ω internally. These RF ports are DC decoupled and require no DC-blocking capacitors or matching components. This helps reduce the system board's Bill of Materials (BOM) cost.

The SST12LP17E is a 2.4 GHz fully-integrated, high-efficiency Power Amplifier module designed in compliance with IEEE 802.11b/g/n applications. It typically provides 28 dB gain with 28% power-added efficiency (PAE) @ POUT = 21.5 dBm for 802.11g and 33% PAE @ POUT = 22 dBm for 802.11b.

The SST12LP17E has excellent linearity, typically ~3% added EVM at 18 dBm output power which is essential for 54 Mbps 802.11g/n operation while meeting 802.11g spectrum mask at 21.5 dBm and 802.11b spectrum mask at 22.5 dBm.

The SST12LP17E also features easy board-level usage along with high-speed power-up/down control through a single combined reference voltage pin. Ultra-low reference current (total $I_{REF} \sim 2$ mA) makes the SST12LP17E controllable by an on/off switching signal directly from the baseband chip. These features, coupled with low operating current, make the SST12LP17E ideal for the final stage power amplification in battery-powered 802.11b/g/n WLAN transmitter applications.

The SST12LP17E has an excellent on-chip, single-ended power detector, which features wide dynamic-range, >15 dB, with dB-wise linear performance. The excellent on-chip power detector provides a reliable solution to board-level power control.

The SST12LP17E is offered in both 8-contact X2SON and 8-contact USON packages. See Figure 2 for pin assignments and Table 1 for pin descriptions.



Functional Blocks

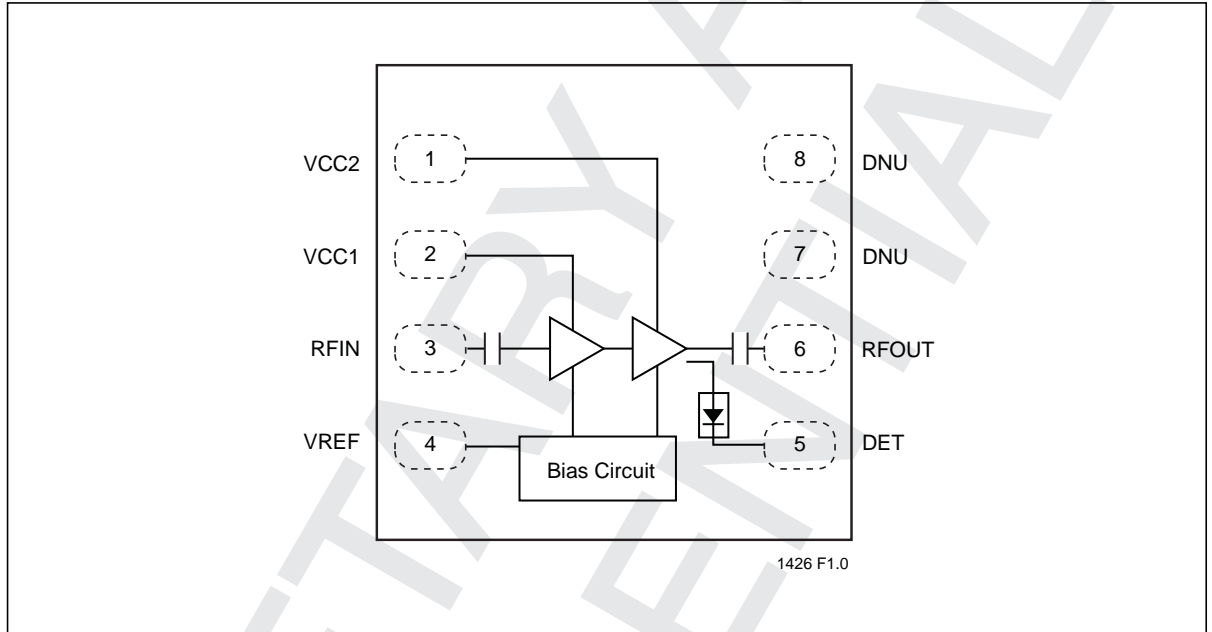


Figure 1: Functional Block Diagram



Pin Assignments

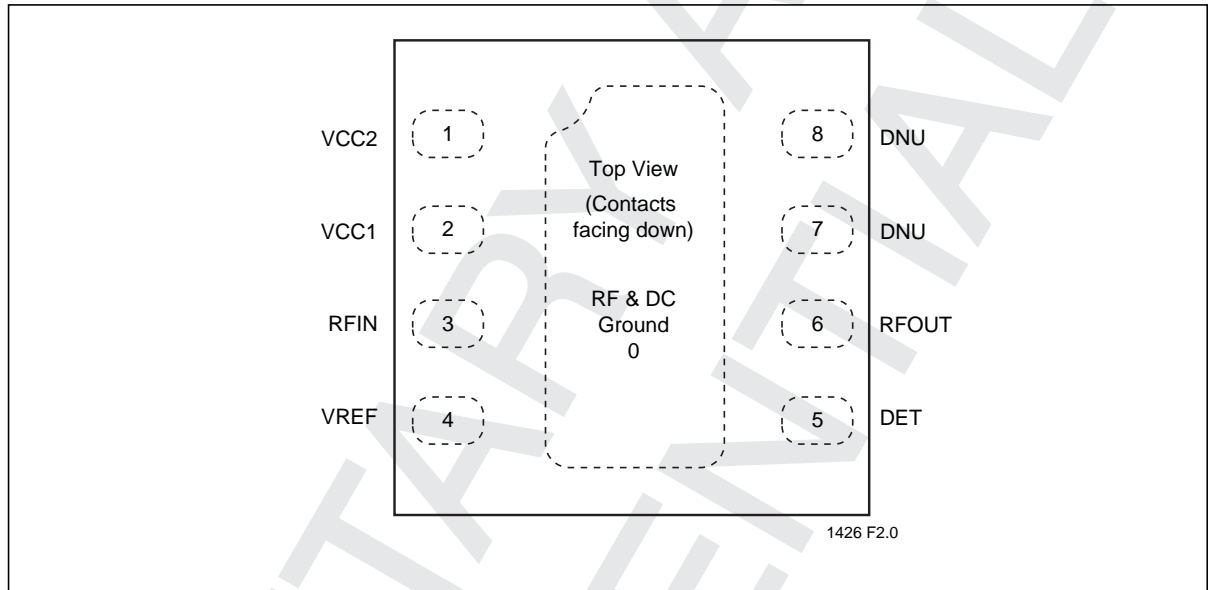


Figure 2: Pin Assignments for 8-contact X2SON and 8-contact USON

Pin Descriptions

Table 1: Pin Description

Symbol	Pin No.	Pin Name	Type ¹	Function
GND	0	Ground		Low inductance ground pad
VCC2	1	Power Supply	PWR	Power supply, 2 nd stage
VCC1	2	Power Supply	PWR	Power supply, 1 st stage
RFIN	3		I	RF input, DC decoupled
VREF	4		PWR	1 st and 2 nd stage idle current control
DET	5		O	On-chip power detector
RFOUT	6		O	RF output, DC decoupled
DNU	7	Do Not Use		Do not use or connect
DNU	8	Do Not Use		Do not use or connect

1. I=Input, O=Output



2.4 GHz High-Efficiency, High-Gain Power Amplifier Module

SST12LP17E

Data Sheet

Electrical Specifications

The DC and RF specifications for the power amplifier are specified below. Refer to Table 3 for the DC voltage and current specifications. Refer to Figures 3 through 8 for the RF performance.

Absolute Maximum Stress Ratings (Applied conditions greater than those listed under “Absolute Maximum Stress Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these conditions or conditions greater than those defined in the operational sections of this data sheet is not implied. Exposure beyond absolute maximum stress rating conditions may affect device reliability.)

Input power to pin 3 (P_{IN})	+5 dBm
Average output power from Pin 6 (P_{OUT}) ¹	+25.5 dBm
Supply Voltage at pins 1 and 2 (V_{CC}) ²	-0.3V to +6.0V
Reference voltage to pin 4 (V_{REF})	-0.3V to +3.3V
DC supply current (I_{CC}) ³	300 mA
Operating Temperature (T_A)	-40°C to +85°C
Storage Temperature (T_{STG})	-40°C to +120°C
Maximum Junction Temperature (T_J)	+150°C
Surface Mount Solder Reflow Temperature	260°C for 10 seconds

- Never measure with CW source. Pulsed single-tone source with <50% duty cycle is recommended. Exceeding the maximum rating of average output power could cause permanent damage to the device.
- V_{CC} maximum rating of 6.0V for RF output power levels up to 10 dBm.
- Measured with 100% duty cycle 54 Mbps 802.11g OFDM Signal

Table 2: Operating Range

Range	Ambient Temp	V_{CC}
Industrial	-40°C to +85°C	3.0V to 4.6V

T2.1 75004

Table 3: DC Electrical Characteristics at 25°C

Symbol	Parameter	Min.	Typ	Max.	Unit
V_{CC}	Supply Voltage at pins 1 and 2	3.0	3.3	4.6	V
I_{CQ}	Idle current to meet EVM ~3% @ 18 dBm Output Power, 802.11g OFDM 54 Mbps signal		60		mA
V_{REG}	Reference Voltage for pin 4		2.9		V
I_{CC}	Current consumption to meet 802.11g OFDM 54 Mbps spectrum mask @ 21.5 dBm		138		mA
	Current consumption to meet 802.11b DSSS 54 Mbps spectrum mask @ 22 dBm		155		mA
	Current consumption to meet EVM ~3% @ 18 dBm Output Power with 802.11g OFDM 54 Mbps signal		105		mA

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2.4 GHz High-Efficiency, High-Gain Power Amplifier Module

SST12LP17E

Data Sheet

Table 4: RF Characteristics at 25°C

Symbol	Parameter	Min.	Typ	Max.	Unit
F _{L-U}	Frequency range	2412		2484	MHz
G	Small signal gain	27	28		dB
G _{VAR1}	Gain variation over band (2412–2484 MHz)			±0.5	dB
G _{VAR2}	Gain ripple over channel (20 MHz)		0.2		dB
2f, 3f, 4f, 5f	Harmonics at 23 dBm, without external filters			-40	dBc
EVM	Added EVM @ 18 dBm output with 802.11g OFDM 54 Mbps signal		3		%
P _{OUT}	Output Power to meet 802.11g OFDM 54 Mbps spectrum mask	20.5	21.5		dBm
	Output Power to meet 802.11b DSSS 1 Mbps spectrum mask	21	22		dBm

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Typical Performance Characteristics

Test Conditions: $V_{CC} = 3.3V$, $T_A = 25^\circ C$, unless otherwise specified

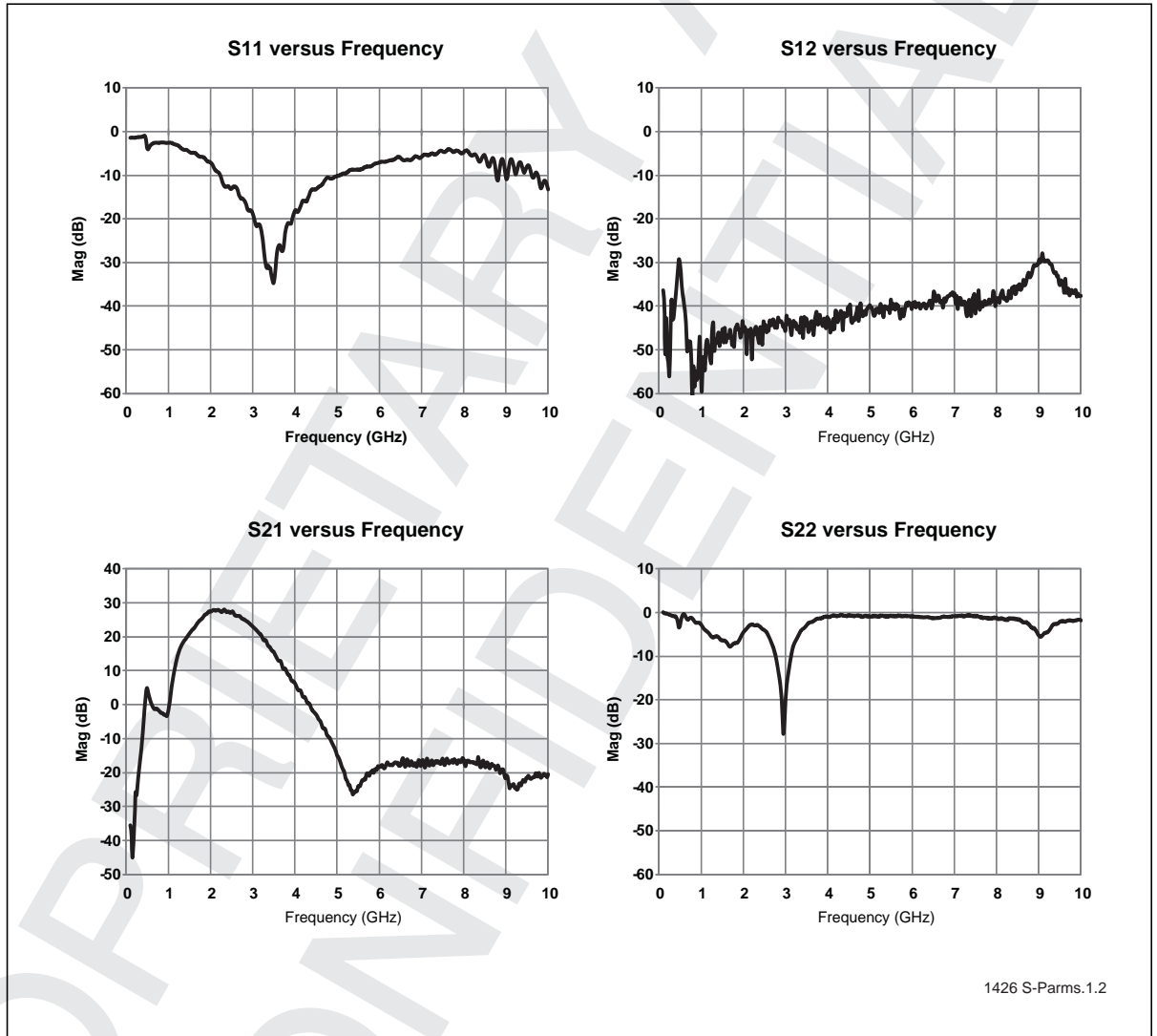


Figure 3: S-Parameters



Typical Performance Characteristics

Test Conditions: $V_{CC} = 3.3V$, $T_A = 25^\circ C$, 54 Mbps 802.11g OFDM Signal Equalizer Training Setting using Channel Estimation Sequence only

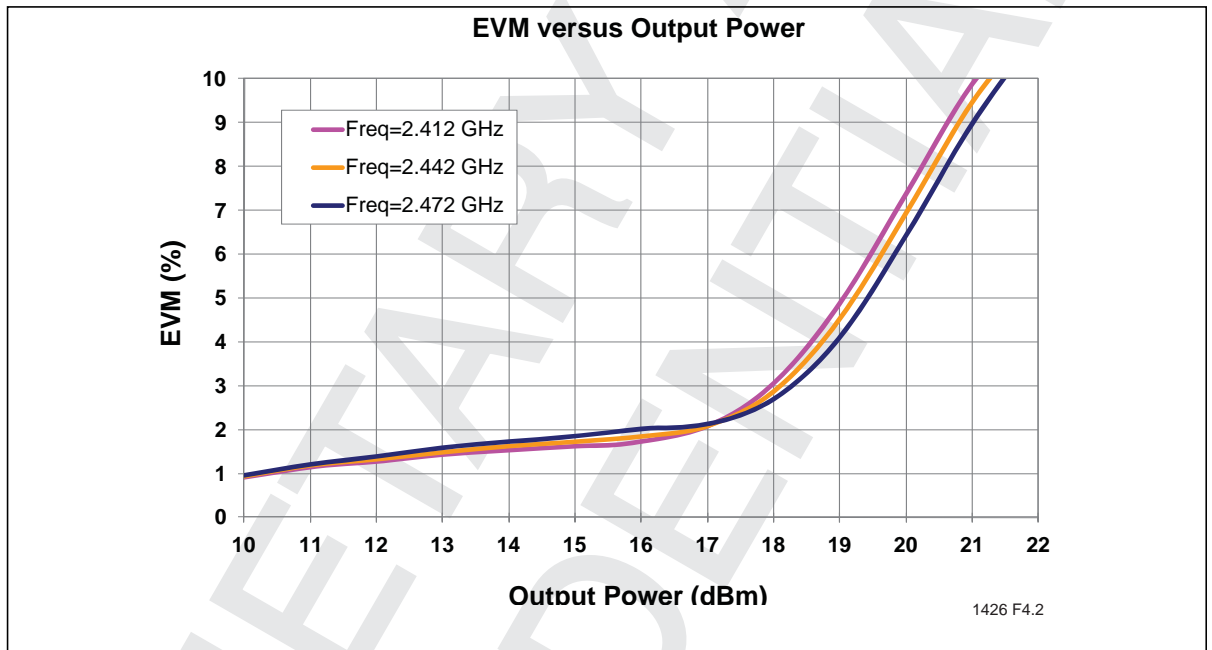


Figure 4: EVM versus Output Power

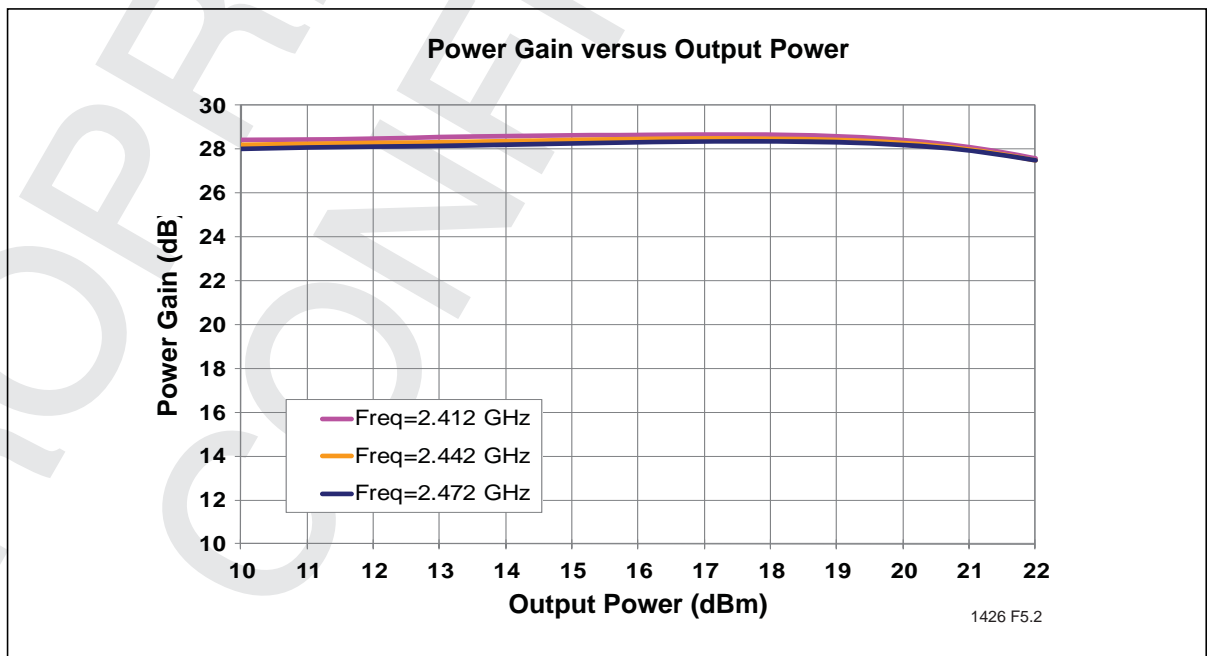


Figure 5: Power Gain versus Output Power

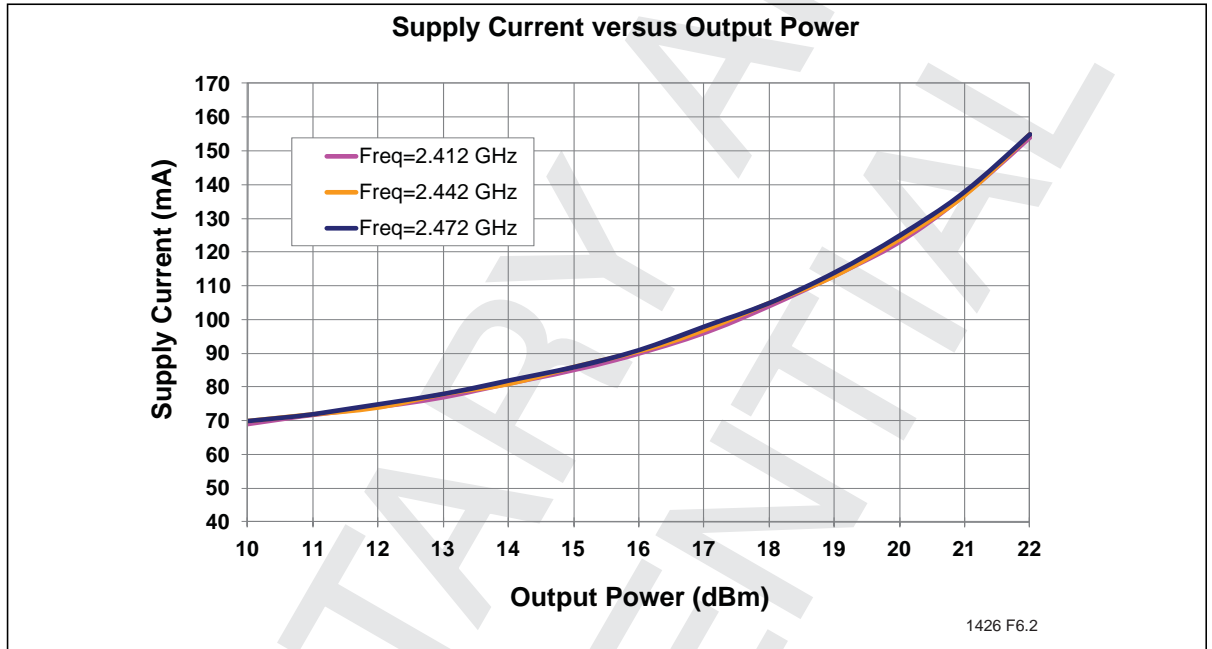


Figure 6: Total Current Consumption for 802.11g operation versus Output Power

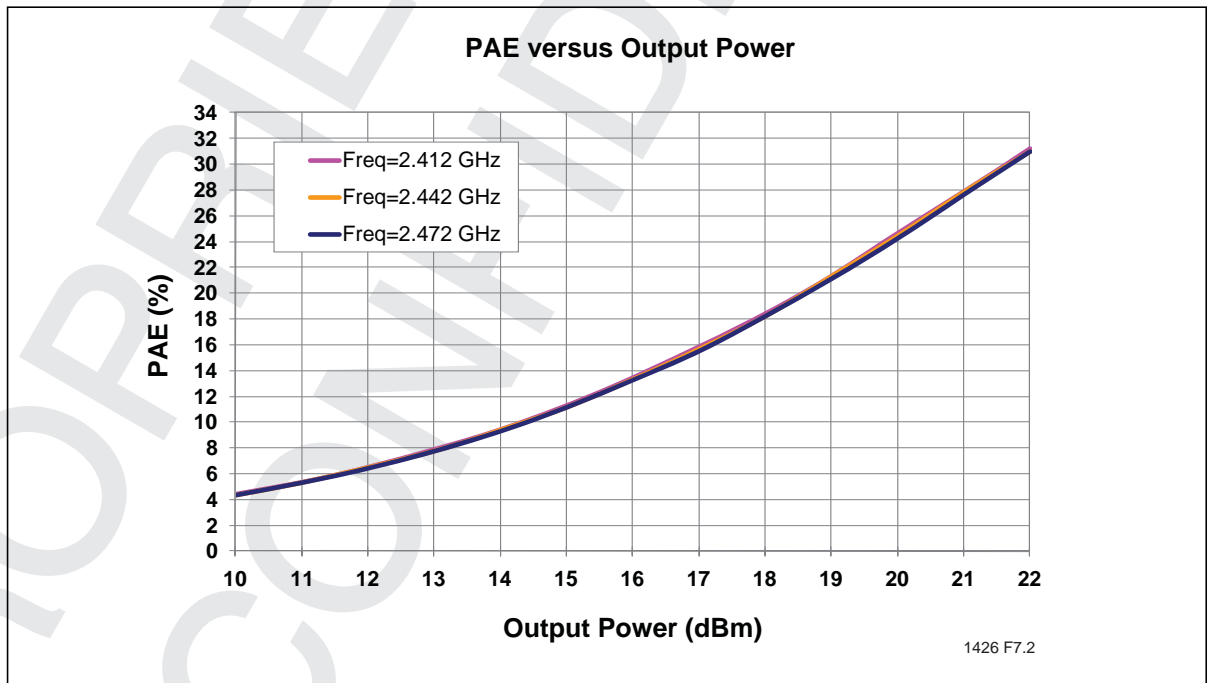


Figure 7: PAE versus Output Power



2.4 GHz High-Efficiency, High-Gain Power Amplifier Module SST12LP17E

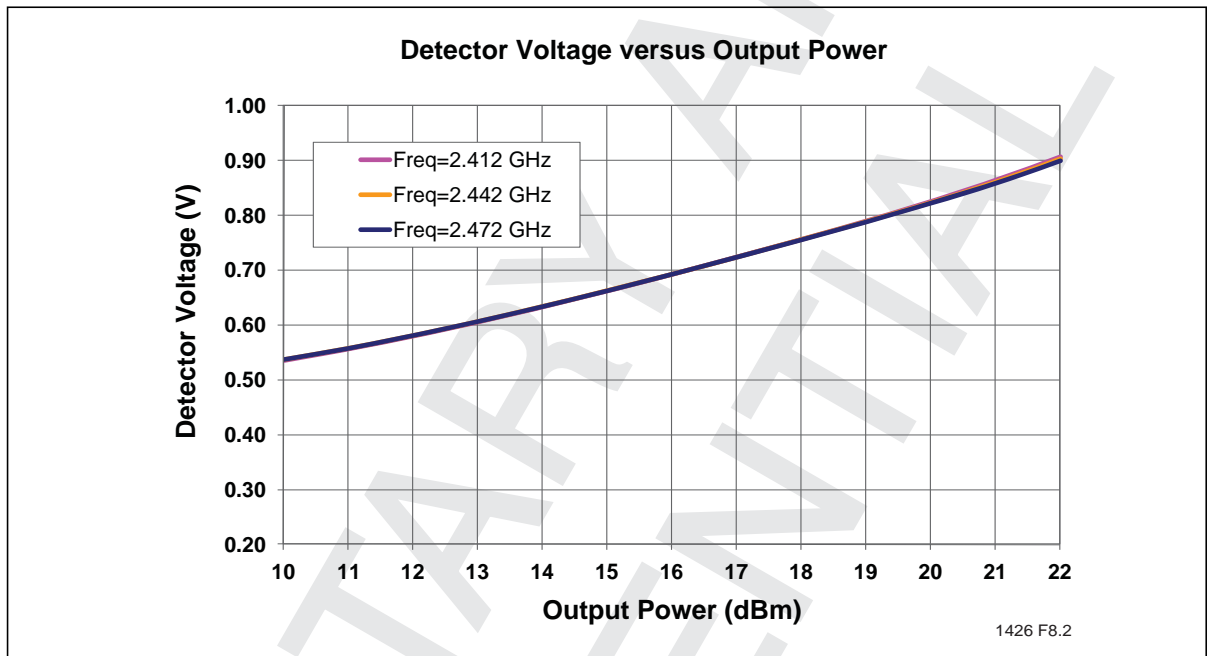


Figure 8: Detector Characteristics versus Output Power

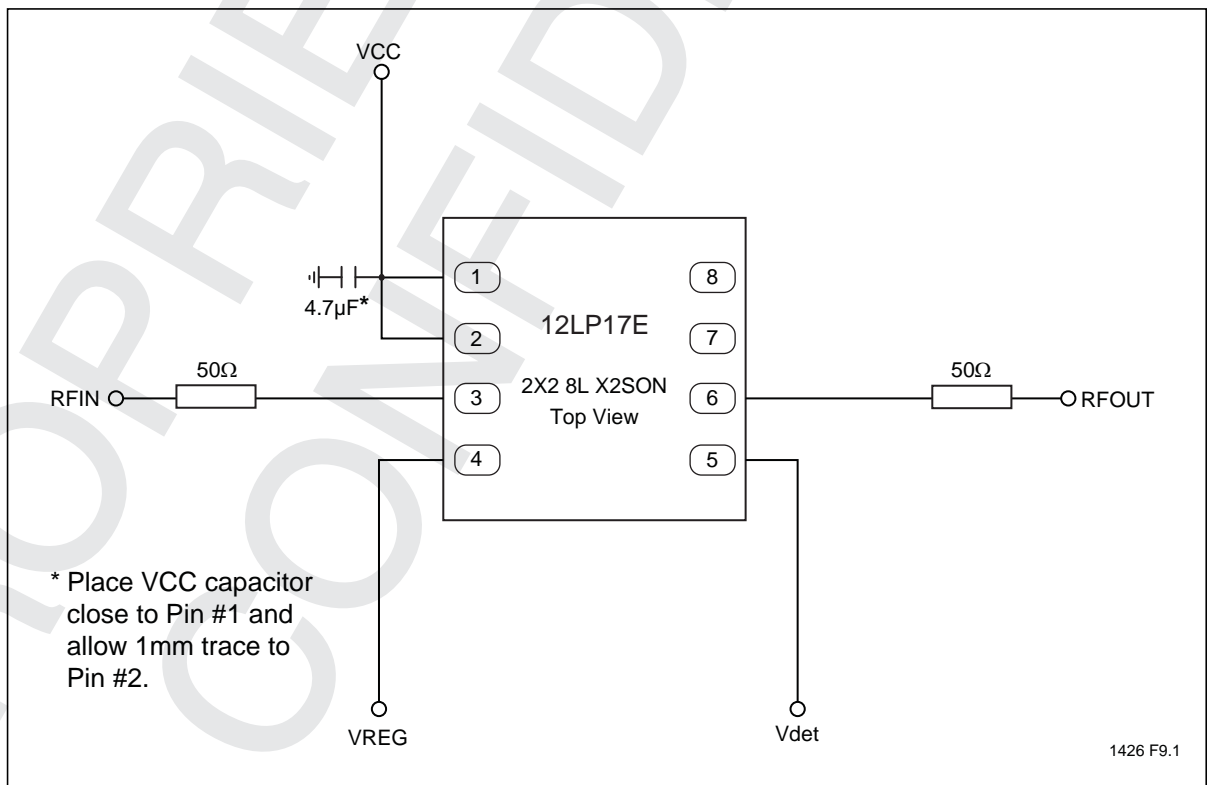
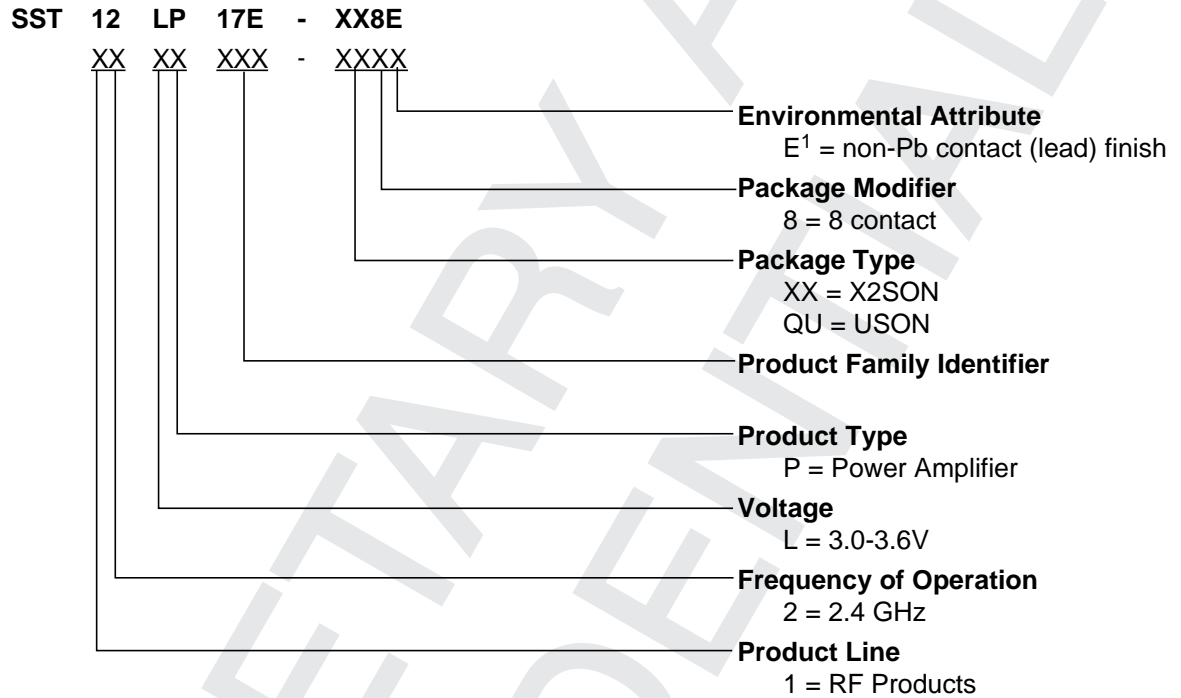


Figure 9: Typical Schematic for High-Efficiency 802.11b/g/n Applications



Product Ordering Information



1. Environmental suffix "E" denotes non-Pb solder. SST non-Pb solder devices are "RoHS Compliant".

Valid combinations for SST12LP17E

SST12LP17E-XX8E SST12LP17E-QU8E

SST12LP17E Evaluation Kits

SST12LP17E-XX8E-K SST12LP17E-QU8E-K

Note: Valid combinations are those products in mass production or will be in mass production. Consult your SST sales representative to confirm availability of valid combinations and to determine availability of new combinations.



Packaging Diagrams

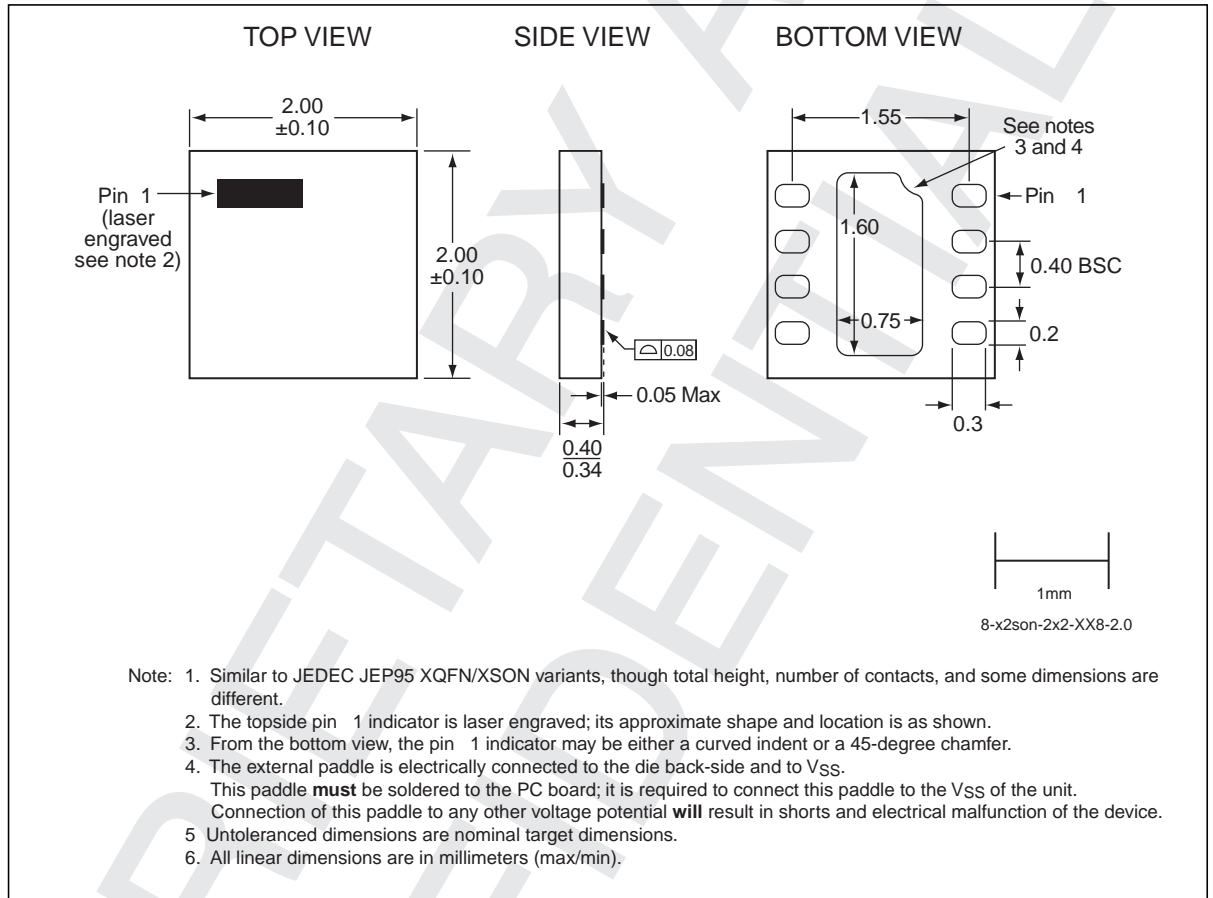


Figure 10: 8-Contact Super-thin Small Outline No-lead (X2SON)
SST Package Code: XX8

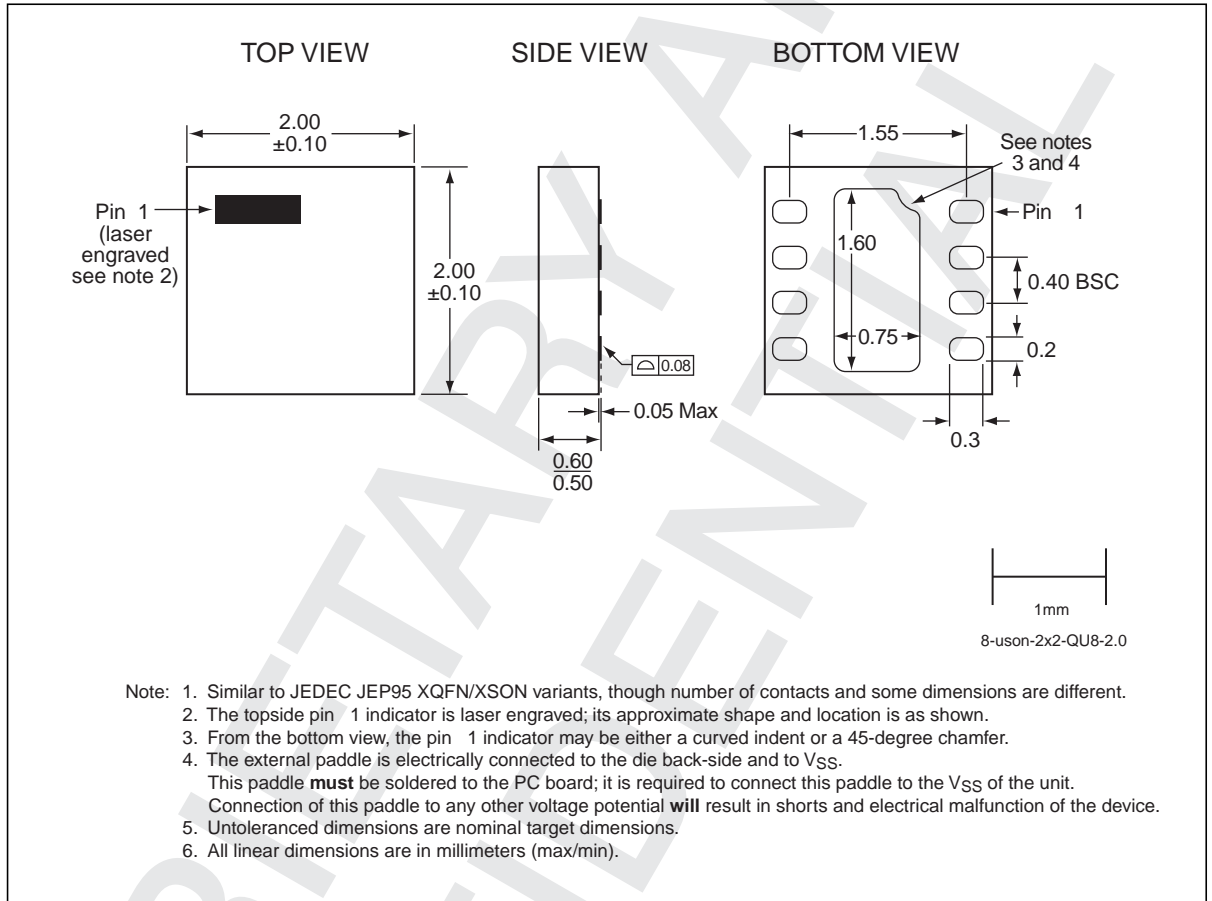


Figure 11: 8-Contact Ultra-thin Small Outline No-lead (USON)
SST Package Code: QU8

**Table 5:** Revision History

Revision	Description	Date
00	<ul style="list-style-type: none"> Initial release of data sheet 	Apr 2010
A	<ul style="list-style-type: none"> Modified “Features”, “Product Description” on page 2, Table 1 on page 4, Table 3 on page 5, Table 4 on page 6, Figure 1 on page 3, and Figure 9 on page 10. Replaced Figures 3-8. 	Apr 2011
B	<ul style="list-style-type: none"> Updated document type to “Data Sheet” Changed supply voltage in “Electrical Specifications” on page 5 Revised VCC values in Table 3 on page 5 	Oct 2011
C	<ul style="list-style-type: none"> Updated package to 8-contact X2SON (XX8) Revised performance information to reflect new package type including Tables 2, 3, and 4 Revised Supply Voltage on page 5. 	Feb 2012
D	<ul style="list-style-type: none"> Added QU8 package information Updated maximum supply voltage from 5.5V to 6.0V in “Absolute Maximum Stress Ratings” on page 5 Updated Supply Voltage from 4.2 to 4.6 in Table 3 on page 5 	Mar 2012
E	<ul style="list-style-type: none"> Updated Figures 10 and 11 to reflect new Pin 1 indicator 	Jul 2012

ISBN:978-1-62076-411-4

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